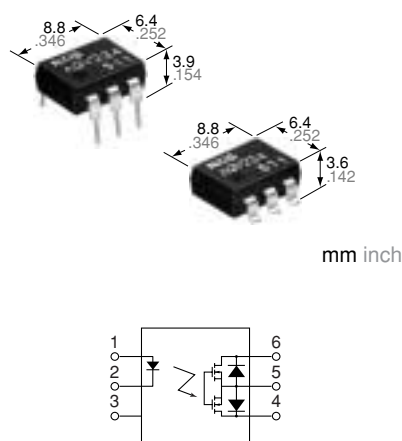


NAiS

**Highest sensitivity
LED operate current:
typical 0.31 A**

**HS PhotoMOS
(AQV234)**



FEATURES

1. High sensitivity type
LED operate current: typical 0.31 mA
2. Low-level off state leakage current
(Typical 1 μ A at 400 V load voltage)
3. Eliminates the need for a power supply to drive the power MOSFET
4. Low thermal electromotive force
(Approx. 1 μ V)
5. Extremely low closed-circuit offset voltages to enable control of small analog signals without distortion
6. Eliminates the need for a counter electromotive force protection diode in the drive circuits on the input side

7. Stable on resistance to help simplify circuit design
8. Surface-mount model available

TYPICAL APPLICATIONS

1. High-speed inspection machines
 - Scanner
 - IC checker
 - Board tester
2. Telephone and data communication equipment

TYPES

Type	Output rating*		Part No.				Packing quantity	
			Through hole terminal	Surface-mount terminal				
	Load voltage	Load current	Tube packing style		Tape and reel packing style		Tube	Tape and reel
					Picked from the 1/2/3-pin side	Picked from the 4/5/6-pin side		
AC/DC type	400 V	120 mA	AQV234	AQV234A	AQV234AX	AQV234AZ	1 tube contains 50 pcs. 1 batch contains 500 pcs.	1,000 pcs.

*Indicate the peak AC and DC values.

Note: For space reasons, the SMD terminal shape indicator "A" and the package type indicator "X" and "Z" are omitted from the seal.

RATING

1. Absolute maximum ratings (Ambient temperature: 25°C 77°F)

Item		Symbol	Type of connection	AQV234(A)	Remarks
Input	LED forward current	I _F		50 mA	
	LED reverse voltage	V _R		5 V	
	Peak forward current	I _{FP}		1 A	f = 100 Hz, Duty factor = 0.1%
	Power dissipation	P _{in}		75 mW	
Output	Load voltage (Peak AC)	V _L		400 V	
	Continuous load current	I _L	A	0.12 A	A connection: Peak AC, DC B, C connection: DC
			B	0.13 A	
			C	0.15 A	
	Peak load current	I _{peak}		0.3 A	A connection: 100 ms (1 shot), V _L = DC
	Power dissipation	P _{out}		500 mW	
Total power dissipation		P _T		550 mW	
I/O isolation voltage		V _{iso}		1,500 V AC	
Temperature limits	Operating	T _{opr}		−40°C to +85°C −40°F to +185°F	Non-condensing at low temperature
	Storage	T _{stg}		−40°C to +100°C −40°F to +212°F	

HS PhotoMOS (AQV234)

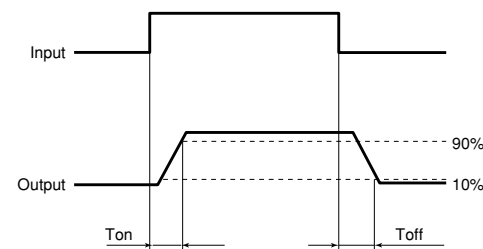
2. Electrical characteristics (Ambient temperature: 25°C 77°F)

Item			Symbol	Type of connection	AQV234(A)	Remarks
Input	LED operate current	Typical	I _{Fon}	—	0.31 mA	ΔI _F /Δt ≥ Min. 100 μA/s I _L = Max.
		Maximum			0.5 mA	
	LED turn off current	Minimum	I _{Foff}	—	0.1 mA	ΔI _F /Δt ≥ Min. 100 μA/s I _L = Max.
		Typical			0.29 mA	
	LED dropout voltage	Typical	V _F	—	1.25 V (1.1 V at I _F = 2 mA)	I _F = 50 mA
		Maximum			1.5 V	
Output	On resistance	Typical	R _{on}	A	30 Ω	I _F = 2 mA I _L = Max. Within 1 s on time
		Maximum			50 Ω	
		Typical	R _{on}	B	22.5 Ω	I _F = 2 mA I _L = Max. Within 1 s on time
		Maximum			25 Ω	
		Typical	R _{on}	C	11.3 Ω	I _F = 2 mA I _L = Max. Within 1 s on time
		Maximum			12.5 Ω	
	Off state leakage current	Maximum	—	—	1 μA	I _F = 0 mA V _L = Max.
	Transistor characteristics	Switching speed	Turn on time*	Typical	T _{on}	0.89 ms
Maximum				2 ms		
Turn off time*			Typical	T _{off}	0.22 ms	I _F = 2 mA I _L = Max.
			Maximum		1 ms	
I/O capacitance		Typical	C _{iso}	0.8 pF	f = 1 MHz V _B = 0 V	
		Maximum		1.5 pF		
Initial I/O isolation resistance		Minimum	R _{iso}	—	1,000 MΩ	500 V DC

Note: Recommendable LED forward current $I_F = 2\text{mA}$.

For type of connection

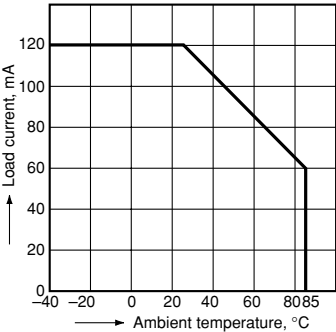
*Turn on/Turn off time



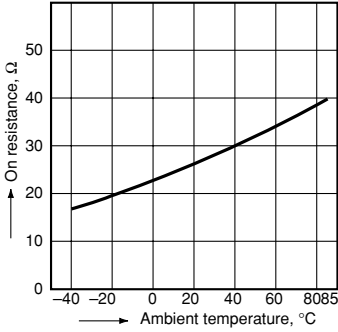
- For Dimensions
- For Schematic and Wiring Diagrams
- For Cautions for Use

REFERENCE DATA

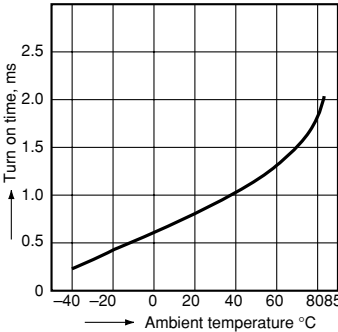
1. Load current vs. ambient temperature characteristics
Allowable ambient temperature: -40°C to $+85^{\circ}\text{C}$
 -40°F to $+185^{\circ}\text{F}$
Type of connection: A



2. On resistance vs. ambient temperature characteristics
Measured portion: between terminals 4 and 6;
LED current: 2 mA; Load voltage: 400 V (DC);
Continuous load current: 120 mA (DC)

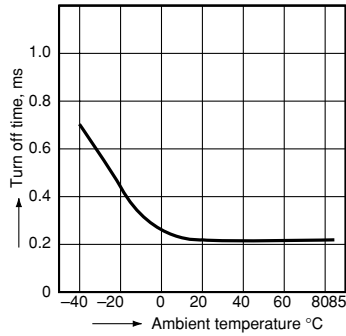


3. Turn on time vs. ambient temperature characteristics
LED current: 2 mA;
Load voltage: 400 V (DC);
Continuous load current: 120 mA (DC)



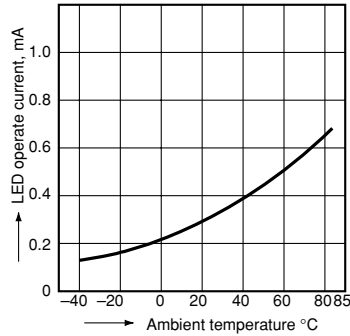
4. Turn off time vs. ambient temperature characteristics

LED current: 2 mA; Load voltage: 400 V (DC);
Continuous load current: 120 mA (DC)



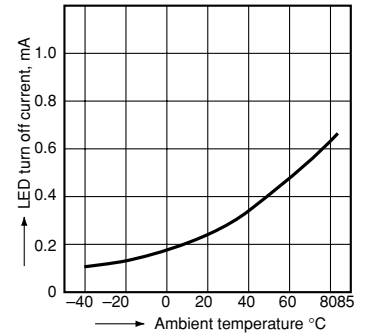
5. LED operate current vs. ambient temperature characteristics

Load voltage: 400 V (DC);
Continuous load current: 120 mA (DC)



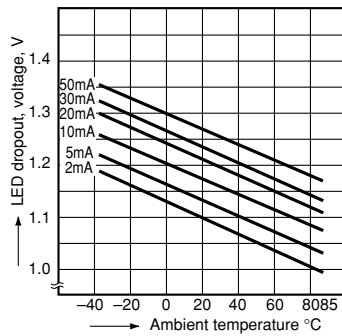
6. LED turn off current vs. ambient temperature characteristics

Load voltage: 400 V (DC);
Continuous load current: 120 mA (DC)



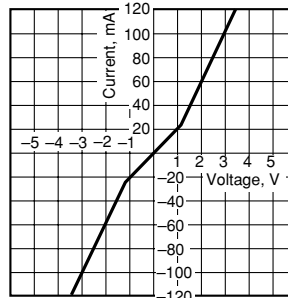
7. LED dropout voltage vs. ambient temperature characteristics

LED current: 2 to 50 mA



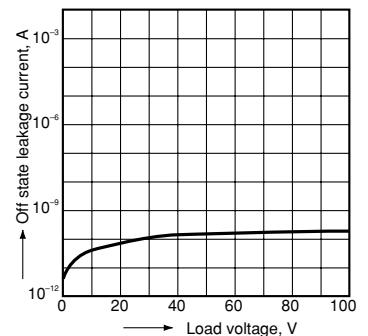
8. Current vs. voltage characteristics of output at MOS portion

Measured portion: between terminals 4 and 6;
Ambient temperature: 25°C 77°F



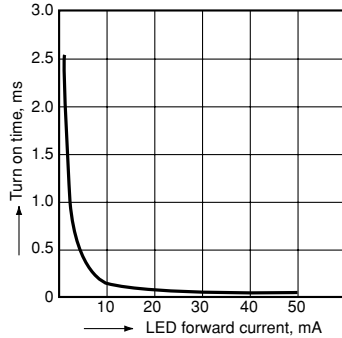
9. Off state leakage current vs. load voltage characteristics

Measured portion: between terminals 4 and 6;
Ambient temperature: 25°C 77°F



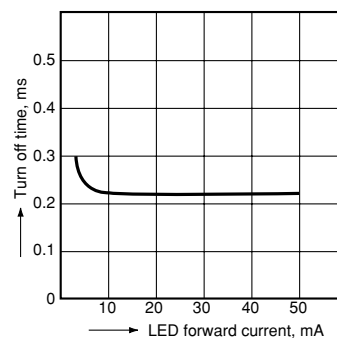
10. Turn on time vs. LED forward current characteristics

Measured portion: between terminals 4 and 6;
Load voltage: 400 V (DC); Continuous load current:
120 mA (DC); Ambient temperature: 25°C 77°F



11. Turn off time vs. LED forward current characteristics

Measured portion: between terminals 4 and 6;
Load voltage: 400 V (DC); Continuous load current:
120 mA (DC); Ambient temperature: 25°C 77°F



12. Output capacitance vs. applied voltage characteristics

Measured portion: between terminals 4 and 6;
Frequency: 1 MHz;
Ambient temperature: 25°C 77°F

